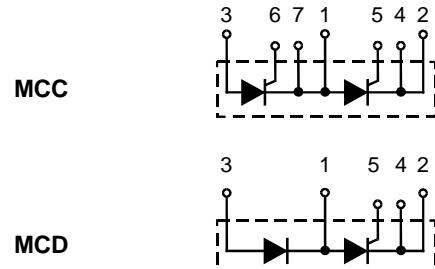
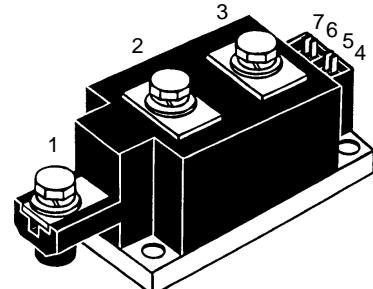


Thyristor Modules

Thyristor/Diode Modules

I_{TRMS} = 2x 400 A
I_{TAVM} = 2x 240 A
V_{RRM} = 2000-2200 V

V _{RSM}	V _{RRM}	Type
V _{DSM}	V _{DRM}	
V	V	
2100	2000	MCC 224-20io1
2300	2200	MCC 224-22io1
		MCD 224-20io1
		MCD 224-22io1



Symbol	Test Conditions		Maximum Ratings	
I _{TRMS}	T _{VJ} = T _{VJM}		400	A
I _{TAVM}	T _C = 85°C; 180° sine		240	A
I _{TSM}	T _{VJ} = 45°C; V _R = 0	t = 10 ms (50 Hz) t = 8.3 ms (60 Hz)	8000	A
			8500	A
	T _{VJ} = T _{VJM} V _R = 0	t = 10 ms (50 Hz) t = 8.3 ms (60 Hz)	7000	A
			7500	A
j ² dt	T _{VJ} = 45°C V _R = 0	t = 10 ms (50 Hz) t = 8.3 ms (60 Hz)	320000	A ² s
			303000	A ² s
	T _{VJ} = T _{VJM} V _R = 0	t = 10 ms (50 Hz) t = 8.3 ms (60 Hz)	245000	A ² s
			240000	A ² s
(di/dt) _{cr}	T _{VJ} = T _{VJM} f = 50 Hz, t _p = 200 µs V _D = 2/3 V _{DRM} I _G = 1 A di _G /dt = 1 A/µs	repetitive, non repetitive, I _T = I _{TAVM}	100	A/µs
			500	A/µs
(dv/dt) _{cr}	T _{VJ} = T _{VJM} ; V _{DR} = 2/3 V _{DRM} R _{gk} = ∞; method 1 (linear voltage rise)		1000	V/µs
P _{GM}	T _{VJ} = T _{VJM} I _T = I _{TAVM}	t _p = 30 µs t _p = 500 µs	120	W
			60	W
P _{GAV}			20	W
V _{RGM}			10	V
T _{VJ}			-40 ... 130	°C
T _{VJM}			130	°C
T _{stg}			-40 ... 125	°C
V _{ISOL}	50/60 Hz, RMS	t = 1 min	3000	V~
	I _{ISOL} ≤ 1 mA	t = 1 s	3600	V~
M _d	Mounting torque (M6)		4.5-7/40-62	Nm/lb.in.
	Terminal connection torque (M8)		11-13/97-115	Nm/lb.in.
Weight	Typical including screws		750	g

Data according to IEC 60747 and refer to a single thyristor/diode unless otherwise stated.
IXYS reserves the right to change limits, test conditions and dimensions

Symbol	Test Conditions	Characteristic Values	
I_{RRM}, I_{DRM}	$T_{VJ} = T_{VJM}; V_R = V_{RRM}$	40	mA
V_T	$I_T = 600 \text{ A}; T_{VJ} = 25^\circ\text{C}$	1.4	V
V_{TO} r_T	For power-loss calculations only ($T_{VJ} = T_{VJM}$)	0.8 0.76	V mΩ
V_{GT}	$V_D = 6 \text{ V}; T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = -40^\circ\text{C}$	2 3	V V
I_{GT}	$V_D = 6 \text{ V}; T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = -40^\circ\text{C}$	150 220	mA mA
V_{GD} I_{GD}	$T_{VJ} = T_{VJM}; V_D = 2/3 V_{DRM}$ $T_{VJ} = T_{VJM}; V_D = 2/3 V_{DRM}$	0.25 10	V mA
I_L	$T_{VJ} = 25^\circ\text{C}; V_D = 6 \text{ V}; t_p = 30 \mu\text{s}$ $di_G/dt = 0.45 \text{ A}/\mu\text{s}; I_G = 0.45 \text{ A}$	200	mA
I_H	$T_{VJ} = 25^\circ\text{C}; V_D = 6 \text{ V}; R_{GK} = \infty$	150	mA
t_{gd}	$T_{VJ} = 25^\circ\text{C}; V_D = 1/2 V_{DRM}$ $di_G/dt = 1 \text{ A}/\mu\text{s}; I_G = 1 \text{ A}$	2	μs
t_q	$T_{VJ} = T_{VJM}; V_R = 100 \text{ V}; V_D = 2/3 V_{DRM}; t_p = 200 \mu\text{s}$ $dv/dt = 50 \text{ V}/\mu\text{s}; I_T = 300 \text{ A}; -di/dt = 10 \text{ A}/\mu\text{s}$	typ. 200	μs
Q_s I_{RM}	$T_{VJ} = T_{VJM}$ $-di/dt = 50 \text{ A}/\mu\text{s}; I_T = 400 \text{ A}$	760 275	μC A
R_{thJC}	per thyristor; DC current	0.139	K/W
	per module	0.069	K/W
R_{thJK}	per thyristor; DC current	0.179	K/W
	per module	0.089	K/W
d_s	Creeping distance on surface	12.7	mm
d_A	Creepage distance in air	9.6	mm
a	Maximum allowable acceleration	50	m/s ²

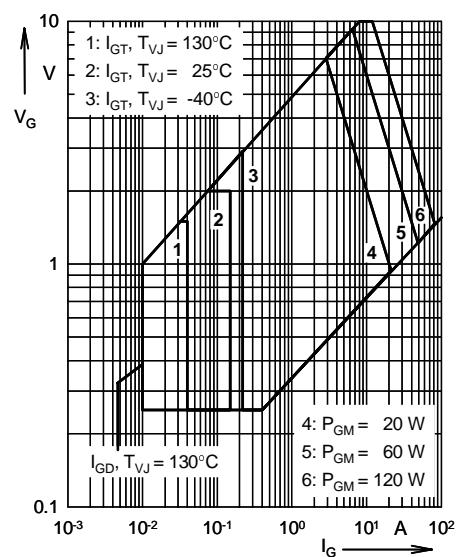


Fig. 1 Gate trigger characteristics

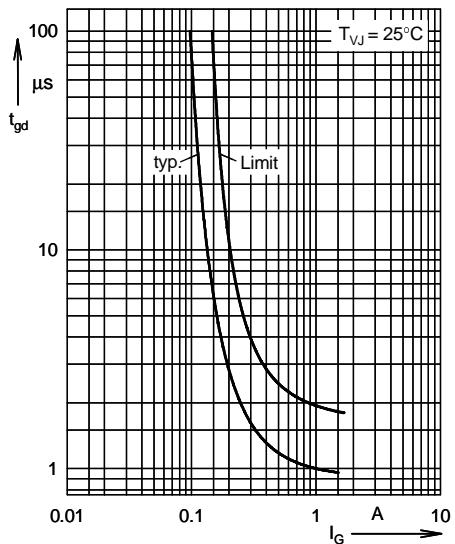
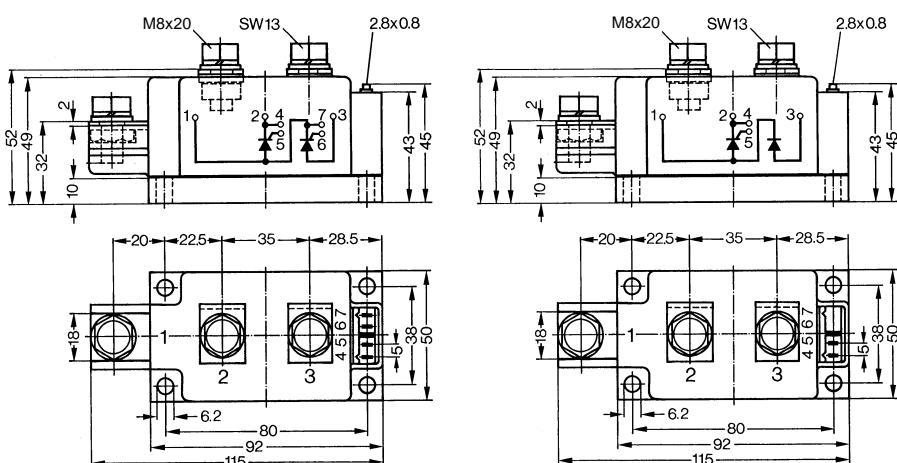


Fig. 2 Gate trigger delay time

Dimensions in mm (1 mm ≈ 0.0394")

MCC

MGD



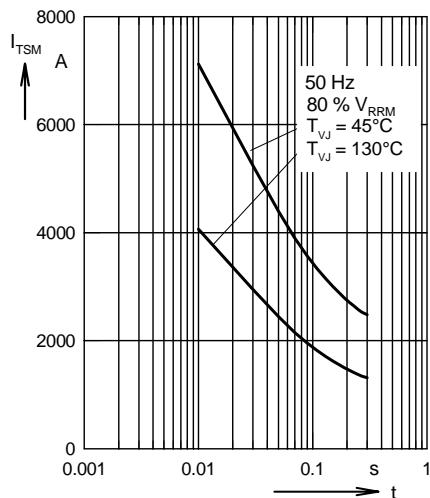


Fig. 3 Surge overload current
 I_{TSM} : Crest value, t : duration

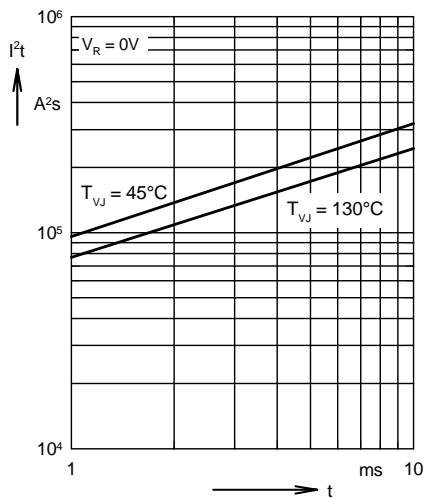


Fig. 4 I^2t versus time (1-10 ms)

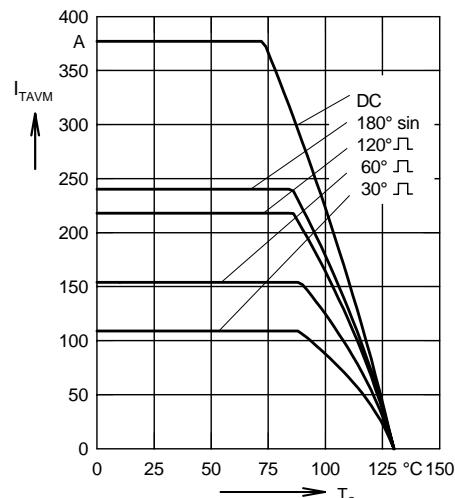


Fig. 4a Maximum forward current
at case temperature

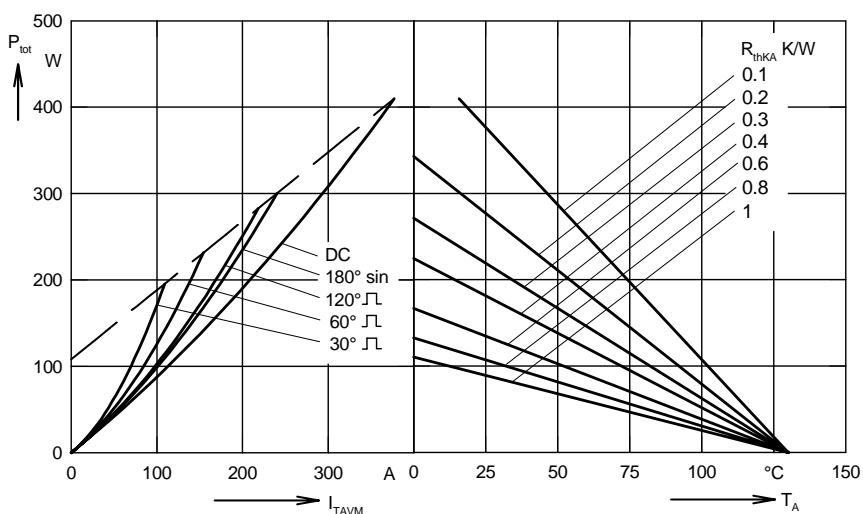


Fig. 5 Power dissipation versus on-state current and ambient temperature (per thyristor or diode)

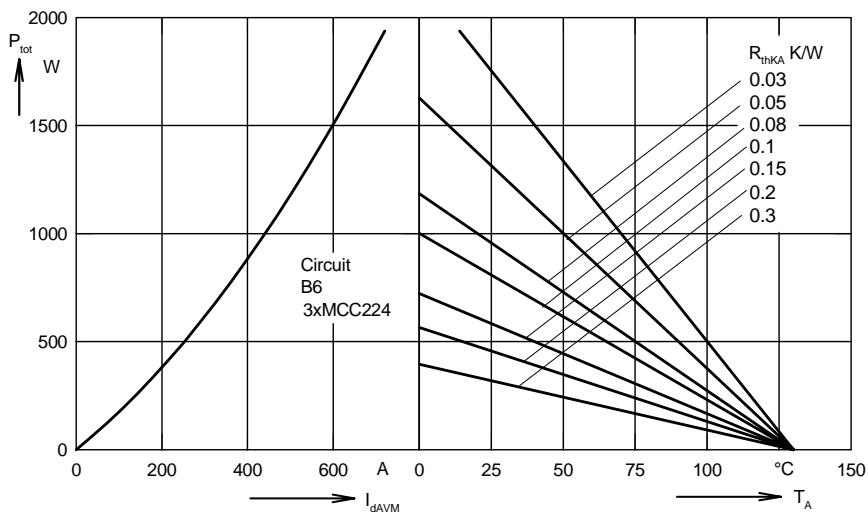


Fig. 6 Three phase rectifier bridge:
Power dissipation versus direct output current and ambient temperature

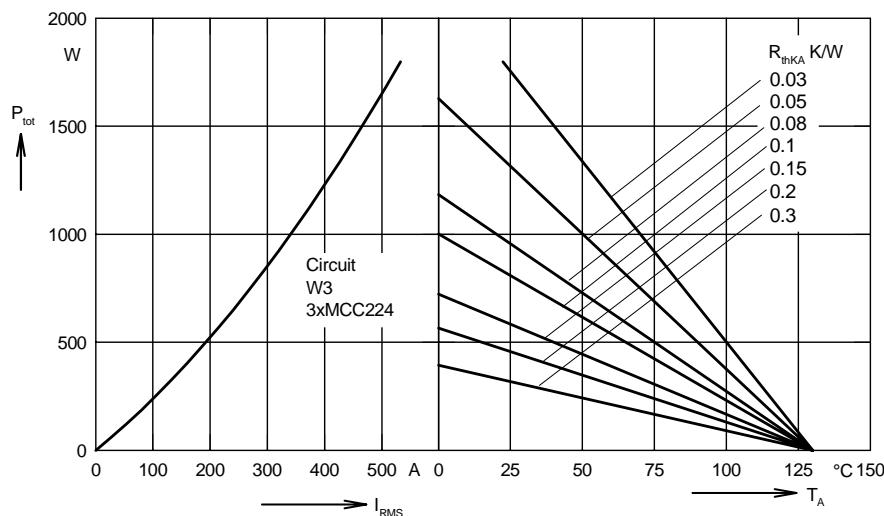


Fig. 7 Three phase AC-controller:
Power dissipation versus RMS
output current and ambient
temperature

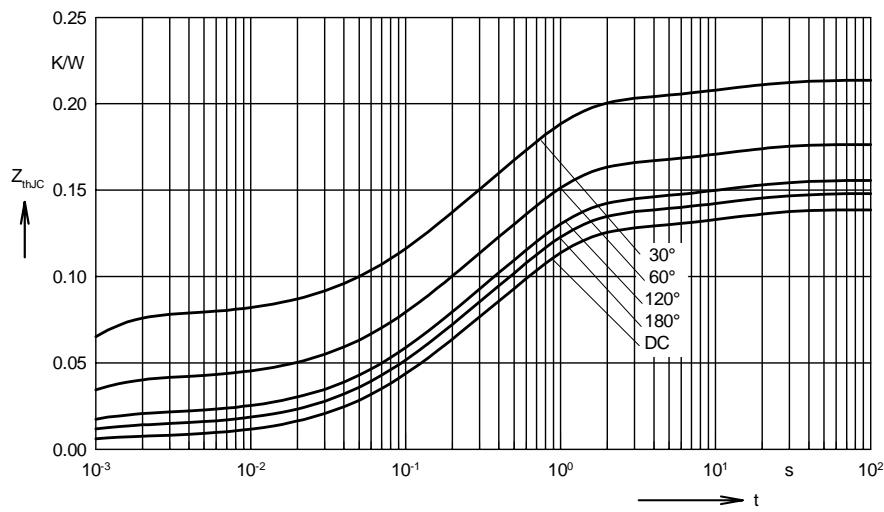


Fig. 8 Transient thermal impedance
junction to case (per thyristor or
diode)

R_{thJC} for various conduction angles d:

d	R_{thJC} (K/W)
DC	0.139
180°	0.148
120°	0.156
60°	0.176
30°	0.214

Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.0067	0.00054
2	0.0358	0.098
3	0.0832	0.54
4	0.0129	12

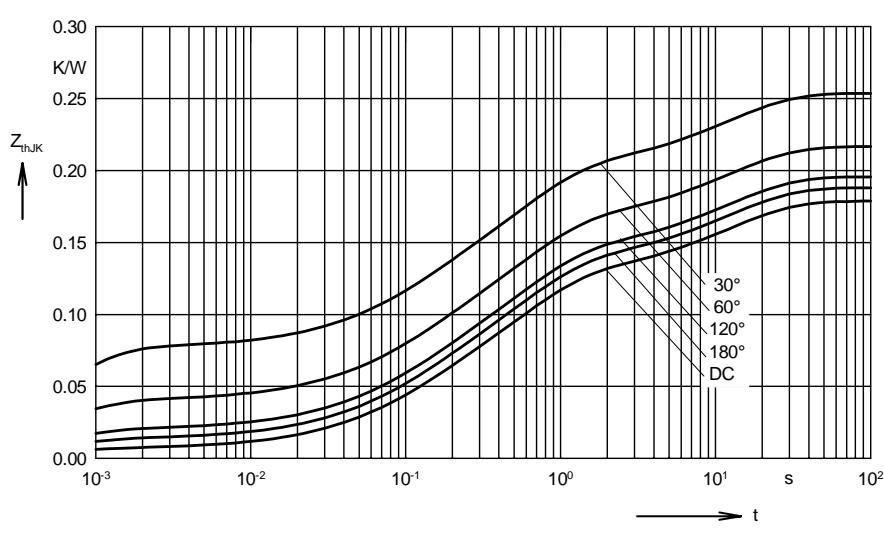


Fig. 9 Transient thermal impedance
junction to heatsink (per thyristor or
diode)

R_{thJK} for various conduction angles d:

d	R_{thJK} (K/W)
DC	0.179
180°	0.188
120°	0.196
60°	0.216
30°	0.256

Constants for Z_{thJK} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.0067	0.00054
2	0.0358	0.098
3	0.0832	0.54
4	0.0129	12
5	0.04	12